

ECE228B
 Spring 2011
 Homework 4 Solutions

10.7 Find ΔV for a change in length, Δl

$$v = c/2nl$$

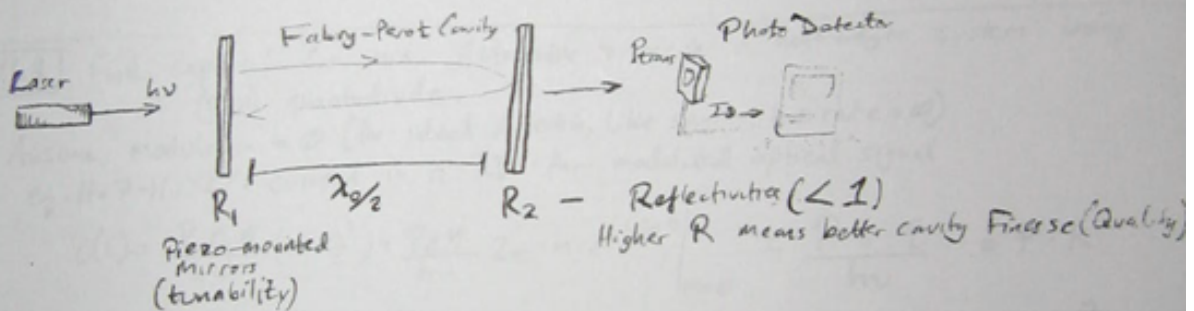
$$v + \Delta v = c/2n(l + \Delta l) \quad // \quad \Delta v = \frac{c}{2n(l + \Delta l)} - v$$

$$\Delta v = \frac{c}{2n(l + \Delta l)} - \frac{c}{2nl} = \frac{lc - (lc - \Delta lc)}{2n(l + \Delta l)l} = \boxed{\frac{-\Delta l \cdot c}{2nl(l + \Delta l)} = \Delta v}$$

10.11 There are numerous ways to measure RMS deviation of a laser spectrum

Construct an F-P cavity designed for maximum transmission @ λ_0 (ω_0), and measure $\Delta P_{transmitted}$ over time to find $\Delta \omega (= \omega(t) - \omega_0)$

Since $(\Delta \omega)_{RMS} = \langle (\omega(t) - \omega_0)^2 \rangle^{1/2}$, use data acquisition software to square the difference, take the time average and square-root the result



When P_{trans} is minimum, $\lambda_{out} = \lambda_0$ ($\omega_{out} = \omega_0$), higher P_{trans} = deviation

- ▷ Determine P_{trans} from I_0
- ▷ P_{trans} related to $\lambda(t)$ ($\omega(t)$) via E-M:

$$E_{trans} = E_0 e^{-jkx} - r_1 r_2 E_0 e^{-jkx + 2\theta} \quad // \quad P_{trans} = \frac{|E_{trans}|^2}{2}$$

Or: Use a prism: Index of Refraction dep. on frequency: $n(\omega)$
 or Diffraction gratings, periodic index change on a mirror

both of which essentially create a "Fourier Transform"; Optical frequency converted to spatial position
 Detect with PD array (or CCD) & analyze Δx with relation to $\Delta \omega$.

11.2 Calculate Minimum Received Power in the presence of large optical background power, P_B for a photoconductor.

If noise term is entirely shot-noise limited:

$$i_N^2 = 2q \cdot I \cdot \Delta V \quad // \quad I = R \cdot P_{opt} = \frac{\eta q}{h\nu} (P_{sig} + P_B)$$

$$i_{sig}^2 = \left(\frac{\eta q}{h\nu}\right)^2 (P_{sig})^2$$

Signal To Noise Ratio:

$$SNR = \frac{i_{sig}^2}{i_N^2} = \frac{R^2 (P_{sig})^2}{2q \cdot R \cdot (P_{sig} + P_B)}$$

[All other noise sources are neglected]

Minimum detectable power is when $i_{sig} = i_N // SNR = 1$

And let $P_B \gg P_{sig}$

$$1 = \frac{R^2 P_{sig}^2}{2q R P_B \Delta V}$$

$\uparrow \eta q/h\nu$

$$// \quad (P_s)_{min} = \left(\frac{2 \cdot P_B \cdot h\nu \cdot \Delta V}{\eta} \right)^{1/2}$$

[typo in question]

11.8 Find expression for min. detectable power in a heterodyne system using a (p-n) photodiode.

Assume modulation = 0 (for ideal detection, like saying, bit rate = 0)
 eq. 11.7-11, Y&Y: current in a P.D. for modulated optical signal

$$i(t) = \frac{P_s \eta}{h\nu} \left(1 + \frac{m^2}{2}\right) + \frac{P_p \eta}{h\nu} 2e \cdot m \cdot e^{i\omega t} \Big|_{m=0} = \frac{P \cdot e \cdot \eta}{h\nu} = P \cdot R$$

for noise currents, shot noise:

$$i_N^2 = 2q \Delta V \cdot I = 2q^2 \frac{P \eta}{h\nu} \Delta V$$

Similar to photomultipliers in heterodyne operation (eq. 11.4-8):

$$SNR = \frac{i_s^2}{i_N^2} = \frac{2(P_s P_L) (e \eta/h\nu)^2}{2q^2 (P_s + P_L) \frac{\eta}{h\nu} \Delta V}$$

[We could have included thermal noise, but it makes no difference to final answer]

[$(P_s P_L)$ from beating of 'local' signal with probe signal, and shot noise is created by $(P_s + P_L)$]

for $(P_s)_{min}$, and $P_L \gg P_s$:

$$SNR = 1 = \frac{P_s \cdot P_L (\eta/h\nu)}{P_L \cdot \Delta V}$$

$$// \quad (P_s)_{min} = \frac{h\nu \cdot \Delta V}{\eta}$$

[Quantum Limit on shot noise. $(P_s)_{min} \uparrow$ for a modulated signal]

⑤ PIN P.D.:

for 8×10^{12} photons, produce 3×10^{12} electrons

A) Find η & R for $\lambda = 830 \text{ nm}, 1300 \text{ nm}, 1550 \text{ nm}$

$$\eta = \frac{\# \text{ electrons}}{\# \text{ photons}} = \frac{3 \times 10^{12}}{8 \times 10^{12}} = \frac{3}{8} = \boxed{37.5\%}$$

$$R = \frac{\eta q}{h\nu} = \frac{\eta q \cdot \lambda}{hc} \left[\begin{array}{l} \text{ignoring} \\ \text{index of} \\ \text{refraction} \\ (n=1) \end{array} \right] \left(\frac{\text{Amps}}{\text{Watt}} \right)$$

$$R @ 830 \text{ nm} = 0.25 \text{ A/W}$$

$$R @ 1300 \text{ nm} = 0.39 \text{ A/W}$$

$$R @ 1550 \text{ nm} = 0.47 \text{ A/W}$$

B) Use Fig 11.15 to find responsivity at $\lambda = 1.3 \mu\text{m}$ for InGaAs P material.

Fig 11.15 is a \log_2 scale, so $1.5(\text{unit}) = 2^{(1.378)} \approx 2^{(1.4)}$

$$\boxed{\eta(\lambda=1.3 \mu\text{m}) \approx 55\%}, \quad R = \eta \left(\frac{q\lambda}{hc} \right) = \boxed{0.577 \left(\frac{\text{A}}{\text{W}} \right) = R}$$

⑥ Si PIN P.D.: $P_{in} = 0 \text{ dBm} = 1 \text{ mW}$, $\lambda = 0.8 \mu\text{m}$, $\text{BW} = \Delta\nu = 20 \text{ MHz}$

$\eta = 0.65$, $i_{dark} = 1 \text{ nA}$, $C = 8 \text{ pF}$

A) Find RMS shot noise current, σ_s^2

$$\sigma_s^2 = \langle i_s^2 \rangle = 2q \cdot \Delta\nu (I_p + I_d) \quad // \quad I_p = R \cdot P_{in} = \left(\frac{\eta q \lambda}{hc} \right) \cdot (1 \text{ mW})$$

$1 \text{ nA} \leftarrow \text{negligible compared to } I_p$

$$\boxed{\langle i_s^2 \rangle = 2.69 \times 10^{-15} \text{ A}^2}$$

$$B) \text{ SNR} = \frac{\langle i_p \rangle^2}{\langle i_s^2 \rangle} = \frac{(P_{in} \cdot R)^2}{2q(P_{in}) \Delta\nu} = \frac{P_{in} R}{2q \Delta\nu} = 65 \times 10^6 \left(\frac{\text{W}}{\text{W}} \right) = \boxed{78.13 \text{ dB}}$$

C) for $\text{SNR}_{min} = 20 \text{ dB}$, find $(P_{in})_{min}$

$$\frac{\langle i_p \rangle^2}{\langle i_s^2 \rangle} = \frac{S}{N} = 10^{20/10} = 100 \left(\frac{\text{W}}{\text{W}} \right) \quad // \quad \langle i_s \rangle^2 = (P_{in} \cdot R)^2 = \langle i_s \rangle^2 \cdot 100 \quad // \quad P_{in} = \sqrt{\langle i_s \rangle^2 \cdot 100} / R$$

$$\text{noise} = \text{shot} \quad P_{in} = \sqrt{\langle i_s \rangle^2 \cdot 100} / R = \sqrt{(2.69 \times 10^{-15}) \cdot 100} / 0.419 \text{ A/W} = \boxed{1.24 \text{ nW}}$$

$$\langle i_{noise} \rangle^2 = 2q \cdot \Delta\nu (P_{in} \cdot R)$$

$$P_{in} \cdot P_{in}^{-1/2} = P_{in}^{1/2} = \sqrt{2q \cdot \Delta\nu \cdot 100 \cdot R^2} / R \quad // \quad (P_{in})_{min} = 2q \cdot \Delta\nu \cdot 100 / (0.419)$$